











**SN65C1168E-SEP** 

SLLSFC4-JULY 2019

# SN65C1168E-SEP Dual Differential Drivers and Receivers With ±12-kV ESD Protection

#### 1 Features

- VID V62/19606
- Radiation hardened
  - Single event latch-up (SEL) immune to 43 MeV-cm<sup>2</sup>/mg at 125°C
  - ELDRS-free to 30 krad(Si)
  - Total ionizing dose (TID) RLAT for every wafer lot up to 20 krad(Si)
- Space Enhanced Plastic
  - Controlled baseline
  - Gold wire
  - NiPdAu lead finish
  - One assembly and test site
  - One fabrication site
  - Available in military (–55°C to 125°C) temperature range
  - Extended product life cycle
  - Extended product-change notification
  - Product traceability
  - Enhanced mold compound for low outgassing
- Meet or exceed standards TIA/EIA-422-B and ITU recommendation V.11
- Operate from single 5-V power supply
- ESD protection for RS-422 bus pins
  - ±12-kV human-body model (HBM)
  - ±8-kV IEC 61000-4-2, contact discharge
  - ±8-kV IEC 61000-4-2, air-gap discharge

- Low-pulse skew
- Receiver input impedance . . . 17 kΩ (typical)
- Receiver input sensitivity . . . ±200 mV
- Receiver common-mode input voltage range of –7 V to 7 V
- Glitch-free power-up/power-down protection

#### 2 Applications

- Support low earth orbit space applications
- Satellite communications
- · AC and servo motor drives

#### 3 Description

The SN65C1168E-SEP consists of dual drivers and dual receivers with ±12-kV ESD (HBM) and ±8-kV ESD (IEC61000-4-2 Air-Gap Discharge and Contact Discharge) for RS-422 bus pins. The device meets the requirements of TIA/EIA-422-B and ITU recommendation V.11. Some parameters do not meet all TIA/EIA-422-B and ITU recommendation V.11 requirements after 20-krad(Si) TID exposure.

The SN65C1168E-SEP drivers have individual activehigh enables.

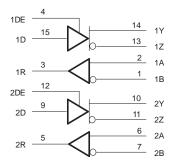
#### Device Information<sup>(1)</sup>

PART NUMBER	PACKAGE	BODY SIZE (NOM)
SN65C1168EMPWTSEP	TCCOD (46)	F 00 mm 4 40 mm
SN65C1168EMPWSEP	TSSOP (16)	5.00 mm × 4.40 mm

<sup>(1)</sup> For all available packages, see the orderable addendum at the end of the data sheet.

#### **Block Diagram**

SN65C1168E-SEP



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## 4 Revision History

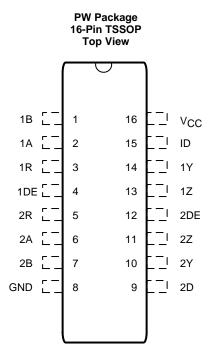
NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
July 2019	*	Initial release.



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## 5 Pin Configuration and Functions



**Pin Functions** 

	PIN	1/0	DESCRIPTION
NAME	NO.	1,0	DESCRIPTION
1A	2	1	RS422 differential input (noninverting) to receiver 1
2A	6	1	RS422 differential input (noninverting) to receiver 2
1B	1	1	RS422 differential input (inverting) to receiver 1
2B	7	1	RS422 differential input (inverting) to receiver 2
1D	15	1	Logic data input to RS422 driver 1
2D	9	1	Logic data input to RS422 driver 2
1DE	4	ı	Driver 1 enable (active high)
2DE	12	I	Driver 2 enable (active high)
GND	8	_	Device ground
1R	3	0	Logic data output of RS422 receiver 1
2R	5	0	Logic data output of RS422 receiver 2
V <sub>CC</sub>	16	_	Power supply
1Y	14	0	RS-422 differential (noninverting) driver output 1
2Y	10	0	RS-422 differential (noninverting) driver output 2
1Z	13	0	RS-422 differential (noninverting) driver output 1
2Z	11	0	RS-422 differential (noninverting) driver output 2

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#### 6 Specifications

#### 6.1 Absolute Maximum Ratings

over recommended operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V <sub>CC</sub>	Supply voltage <sup>(2)</sup>		-0.5	7	V
\/	Input voltage	Driver, DE, RE	-0.5	7	V
VI	Input voltage	A or B, Receiver	-14	14	V
$V_{\text{ID}}$	Differential input voltage <sup>(3)</sup>	Receiver	-14	14	V
\/	Output voltage	Driver	-0.5	7	\ /
Vo		Receiver	-0.5	V <sub>CC</sub> + 0.5	V
I <sub>IK</sub>	Input clamp current	Driver, V <sub>I</sub> < 0		-20	mA
		Driver, V <sub>O</sub> < 0		-20	A
I <sub>OK</sub>	Output clamp current	Receiver	-20	20	mA
	Output surrent	Driver	-150	150	A
Io	Output current	Receiver	-25	25	mA
Icc	Supply current			200	mA
	GND current			-200	mA
TJ	Operating virtual junction temperature			150	°C
T <sub>stg</sub>	Storage temperature		-65	150	°C

<sup>(1)</sup> Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

#### 6.2 ESD Ratings

			VALUE	UNIT
		Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±12000	
V	Electrostatic discharge IEC 61	Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±1000	V
V <sub>(ESD)</sub>		IEC 61000-4-2, air-gap discharge	±8000	V
		IEC 61000-4-2, contact discharge	±8000	

<sup>1)</sup> JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.

<sup>(2)</sup> All voltage values except differential input voltage are with respect to the network GND.

<sup>3)</sup> Differential input voltage is measured at the noninverting terminal, with respect to the inverting terminal.

<sup>(2)</sup> JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.



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6.3 Recommended Operating Conditions

			MIN	NOM	MAX	UNIT
V <sub>CC</sub>	Supply voltage		4.5	5	5.5	V
$V_{IC}$	Common-mode input voltage (1)	Receiver			±7	V
$V_{\text{ID}}$	Differential input voltage	Receiver			±7	V
VI	Input voltage	Except A, B	0		5.5	V
Vo	Output voltage	Receiver	0		V <sub>CC</sub>	V
$V_{IH}$	High-level input voltage	Except A, B	2			V
$V_{IL}$	Low-level input voltage	Except A, B			8.0	V
	High level output ourrent	Receiver			-6	A
I <sub>OH</sub>	High-level output current	Driver			-20	mA
	High-level input voltage Except A, B  Low-level input voltage Except A, B  High-level output current Receiver			6	A	
I <sub>OL</sub>				20	mA	
T <sub>A</sub>	Operating free-air temperature		-55		125	°C

<sup>(1)</sup> Refer to TIA/EIA-422-B for exact conditions.

#### 6.4 Thermal Information

		SN65C1168E-SEP	
	THERMAL METRIC <sup>(1)</sup>	PW (TSSOP)	UNIT
		16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	102.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	32.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	48.8	°C/W
ΨЈТ	Junction-to-top characterization parameter	1.8	°C/W
ΨЈВ	Junction-to-board characterization parameter	48.2	°C/W
R <sub>0</sub> JC(bot)	Junction-to-case (bottom) thermal resistance	N/A	°C/W

<sup>(1)</sup> For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report, SPRA953.

Product Folder Links: SN65C1168E-SEP

## **ISTRUMENTS**

### 6.5 Driver Section Electrical Characteristics

over recommended supply voltage and operating free-air temperature ranges (unless otherwise noted)

	PARAMETER	TEST	CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
V <sub>IK</sub>	Input clamp voltage	$I_{I} = -18 \text{ mA}$				-1.5	V
V <sub>OH</sub>	High-level output voltage	$V_{IH} = 2 \text{ V}, V_{IL} = 0.8 \text{ V}$	V, I <sub>OH</sub> = −20 mA	2.4	3.5		V
V <sub>OL</sub>	Low-level output voltage	$V_{IH} = 2 \text{ V}, V_{IL} = 0.8 \text{ V}$	V, I <sub>OL</sub> = 20 mA		0.2	0.4	V
V <sub>OD1</sub>	Differential output voltage 1	$I_O = 0 \text{ mA}$		2		6	V
V <sub>OD2</sub>	Differential output voltage 2	$R_L = 100 \Omega$ , see Figure	ure 1 <sup>(2)</sup>	2	3.7		V
$\Delta  V_{OD} $	Change in magnitude of differential output voltage	$R_L = 100 \Omega$ , see Figure	ure 1 <sup>(2)</sup>	-0.4		0.4	V
V <sub>OC</sub>	Common-mode output voltage	$R_L = 100 \Omega$ , see Figure	ure 1 <sup>(2)</sup>	-3		3	V
Δ V <sub>OC</sub>	Change in magnitude of common-mode output voltage	$R_L = 100 \Omega$ , see Figure	ure 1 <sup>(2)</sup>	-0.4		0.4	V
	0	.,	V <sub>O</sub> = 6 V			100	
I <sub>O(OFF)</sub>	Output current with power off	$V_{CC} = 0 V$	V <sub>O</sub> = -0.25 V			100	μΑ
	Output surrent with some off(3)	V 0.V	V <sub>O</sub> = 6 V			3	Α
I <sub>O(OFF)</sub>	Output current with power off (3)	$V_{CC} = 0 V$	V <sub>O</sub> = -0.25 V			3	mA
	I Park Consideration and the system of the system of	V <sub>O</sub> = 2.5 V				20	^
l <sub>OZ</sub>	High-impedance-state output current	V <sub>O</sub> = 5 V				-20	μΑ
	High important subject to the second subject (3)	V <sub>O</sub> = 2.5 V				2	A
l <sub>OZ</sub>	High-impedance-state output current <sup>(3)</sup>	V <sub>O</sub> = 5 V				-2	mA
I <sub>IH</sub>	High-level input current	$V_I = V_{CC}$ or $V_{IH}$				1	μΑ
I <sub>IL</sub>	Low-level input current	$V_I = GND \text{ or } V_{IL}$				-36	μΑ
Ios	Short-circuit output current	$V_O = V_{CC}$ or $GND^{(4)}$		-30		-160	mA
	Complete support (total populars)	No load,	$V_I = V_{CC}$ or GND		4	6	A
I <sub>CC</sub>	Supply current (total package)	Enabled	$V_I = 2.4 \text{ or } 0.5 \text{ V}^{(5)}$		5	9	mA
	Supply ourrent (total pookage) (3)	No load,	V <sub>I</sub> = V <sub>CC</sub> or GND			17 16	mA
I <sub>CC</sub>	Supply current (total package) (3)	Enabled	V <sub>I</sub> = 2.4 or 0.5 V <sup>(5)</sup>				MA
C <sub>i</sub>	Input capacitance				6		pF

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All typical values are at  $V_{CC}$  = 5 V and  $T_A$  = 25°C. Refer to TIA/EIA-422-B for exact conditions. 25°C only. Post 20-krad(Si) HDR TID using worst case static biasing.

Not more than one output should be shorted at a time, and the duration of the short circuit should not exceed one second. This parameter is measured per input, while the other inputs are at  $V_{CC}$  or GND.



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### 6.6 Receiver Section Electrical Characteristics

over recommended ranges of common-mode input voltage, supply voltage, and operating free-air temperature (unless otherwise noted)

(unics	s otherwise noted)						
	PARAMETER	TEST (	CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
V <sub>IT+</sub>	Positive-going input threshold voltage, differential input					0.2	V
$V_{\text{IT-}}$	Negative-going input threshold voltage, differential input			-0.2 <sup>(2)</sup>			V
$V_{hys}$	Input hysteresis (V <sub>IT+</sub> - V <sub>IT-</sub> )				60		mV
$V_{OH}$	High-level output voltage	$V_{ID}$ = 200 mV, $I_{OH}$	= -6 mA	3.8	4.2		V
$V_{OL}$	Low-level output voltage	$V_{ID} = -200 \text{ mV}, I_{OI}$	L = 6 mA		0.1	0.3	V
	Line input surrent	Other input at 0 V	V <sub>I</sub> = 10 V			1.5	mA
II	Line input current	Other input at 0 v	$V_I = -10 \text{ V}$			-2.5	mA
r <sub>l</sub>	Input resistance	$V_{IC} = -7 \text{ V to } 7 \text{ V},$	other input at 0 V	4	17		kΩ
	Cumply augment (total poolsons)	No load,	$V_I = V_{CC}$ or GND		4	6	mA
I <sub>CC</sub>	Supply current (total package)	Enabled	$V_{IH} = 2.4 \text{ V or } 0.5 \text{ V}^{(3)}$		5	9	IIIA
	Supply current (total package) <sup>(4)</sup>	Nolood	$V_I = V_{CC}$ or GND			17	A
I <sub>CC</sub>	Supply current (total package)	No load	V <sub>I</sub> = 2.4 or 0.5 V <sup>(5)</sup>			16	mA

#### 6.7 Driver Section Switching Characteristics

over recommended supply voltage and operating free-air temperature ranges (unless otherwise noted)

	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(1)</sup>	MAX	UNIT
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	$R1 = R2 = 50 \Omega$ , $R3 = 500 \Omega$ ,		8	16	ns
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	C1 = C2 = C3 = 40  pF, S1  is open,		8	16	ns
t <sub>sk(p)</sub>	Pulse skew	see Figure 2		1.5	4	ns
t <sub>r</sub>	Rise time	R1 = R2 = $50 \Omega$ , R3 = $500 \Omega$ ,		5	8	ns
t <sub>f</sub>	Fall time	C1 = C2 = C3 = 40 pF, S1 is open, see Figure 3		5	8	ns
t <sub>PZH</sub>	Output-enable time to high level	R1 = R2 = $50 \Omega$ , R3 = $500 \Omega$ ,		10	19	ns
t <sub>PZL</sub>	Output-enable time to low level	C1 = C2 = C3 = 40 pF, S1 is closed, see Figure 4		10	19	ns
$t_{PHZ}$	Output-disable time from high level	R1 = R2 = $50 \Omega$ , R3 = $500 \Omega$ ,		7	16	ns
t <sub>PLZ</sub>	Output-disable time from low level	C1 = C2 = C3 = 40 pF, S1 is closed, see Figure 4		7	16	ns
f <sub>SW</sub>	Maximum switching frequency	R1 = R2 = 50 $\Omega$ , R3 = 500 $\Omega$ , C1 = C2 = C3 = 40 pF, S1 is open, see Figure 3	20			MHz

(1) All typical values are at  $V_{CC} = 5 \text{ V}$  and  $T_A = 25 ^{\circ}\text{C}$ .

All typical values are at  $V_{CC}$  = 5 V and  $T_A$  = 25°C. The algebraic convention, where the less positive (more negative) limit is designated as minimum, is used in this data sheet for common-mode input voltage and threshold voltage levels only.

Refer to TIA/EIA-422-B for exact conditions.

<sup>25°</sup>C only. Post 20-krad(Si) HDR TID using worst case static biasing.

This parameter is measured per input, while the other inputs are at V<sub>CC</sub> or GND.



## 6.8 Receiver Section Switching Characteristics

over recommended operating free-air temperature range (unless otherwise noted)(1)

				(2)		
	PARAMETER	TEST CONDITIONS	MIN	TYP <sup>(2)</sup>	MAX	UNIT
t <sub>PLH</sub>	Propagation delay time, low- to high-level output	See Figure 5	9	15	27	ns
t <sub>PHL</sub>	Propagation delay time, high- to low-level output	See Figure 5	9	15	27	ns
t <sub>TLH</sub>	Transition time, low- to high-level output	V <sub>IC</sub> = 0 V, see Figure 5		4	9	ns
t <sub>PHL</sub>	Transition time, high- to low-level output			4	9	ns

(1) Measured per input while the other inputs are at  $V_{CC}$  or GND.

(2) All typical values are at  $V_{CC} = 5 \text{ V}$  and  $T_A = 25^{\circ}\text{C}$ .

**ISTRUMENTS** 

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#### 7 Parameter Measurement Information

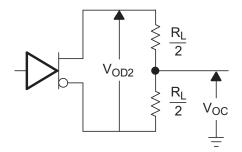
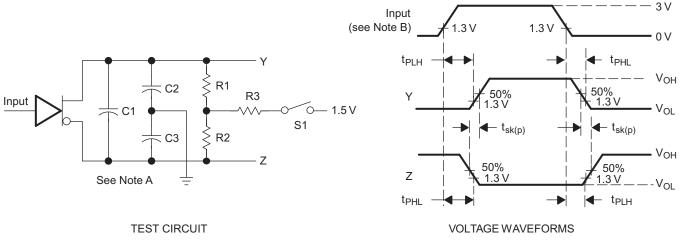
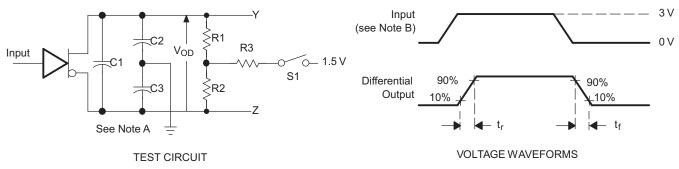


Figure 1. Driver Test Circuit,  $V_{\text{OD}}$  and  $V_{\text{OC}}$ 



- A. C1, C2, and C3 include probe and jig capacitance.
- B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, t<sub>r</sub> = t<sub>f</sub> ≤ 6 ns.

Figure 2. Driver Test Circuit and Voltage Waveforms



- A. C1, C2, and C3 include probe and jig capacitance.
- B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%,  $t_r = t_f \le 6$  ns.

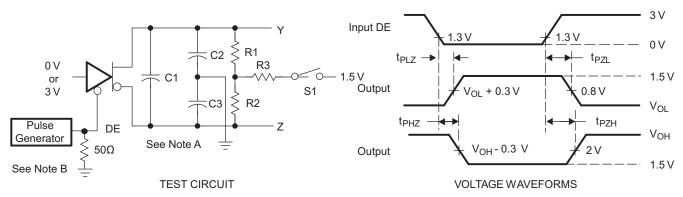
Figure 3. Driver Test Circuit and Voltage Waveforms

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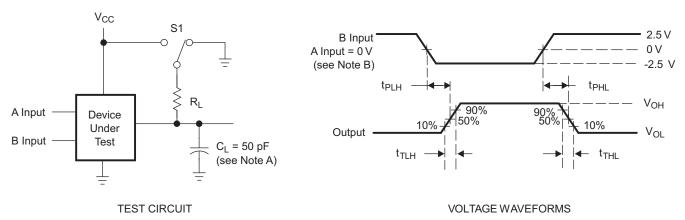
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### **Parameter Measurement Information (continued)**



- A. C1, C2, and C3 include probe and jig capacitance.
- B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%,  $t_r = t_f$  < 6 ns

Figure 4. Driver Test Circuit and Voltage Waveforms



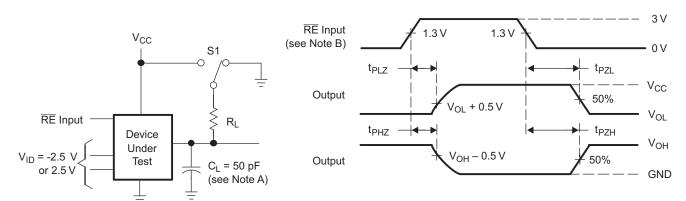
- A. C1, C2, and C3 include probe and jig capacitance.
- B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%,  $t_r = t_f \le 6$  ns.

Figure 5. Receiver Test Circuit and Voltage Waveforms



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Parameter Measurement Information (continued)



 $t_{PZL},\,t_{PLZ}$  Measurement: S1 to V  $_{CC}$   $t_{PZH},\,t_{PHZ}$  Measurement: S1 to GND

**TEST CIRCUIT** 

**VOLTAGE WAVEFORMS** 

- A. C1, C2, and C3 include probe and jig capacitance.
- B. The input pulse is supplied by a generator having the following characteristics: PRR = 1 MHz, duty cycle = 50%, t<sub>r</sub> = t<sub>f</sub> ≤ 6 ns.

Figure 6. Receiver Test Circuit and Voltage Waveforms

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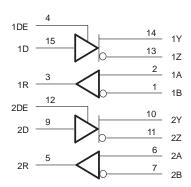
#### 8 Detailed Description

#### 8.1 Overview

The SN65C1168E-SEP consist of dual drivers and dual receivers powered from a single 5-V supply. This device meets the requirements of TIA/EIA-422-B and ITU recommendation V.11.

#### 8.2 Functional Block Diagram





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#### 8.3 Feature Description

#### 8.3.1 Active High Driver Output Enables

SN65C1168E-SEP drivers can be configured individually by 1DE and 2DE logic inputs. Both drivers are set at high-impedance when disabled.



#### 8.4 Device Functional Modes

Table 1 and Table 2 lists the functional modes of SN65C1168E-SEP.

Table 1. Each Driver<sup>(1)</sup>

INPUT	ENABLE	OUTPUTS				
D	DE	Y	Z			
Н	Н	Н	L			
L	Н	L	Н			
X	L	Z	Z			

(1) H = High level, L = Low level, X = Irrelevant, Z = High impedance (off)

Table 2. Each Receiver<sup>(1)</sup>

DIFFERENTIAL INPUTS A-B	OUTPUT R
V <sub>ID</sub> ≥ 0.2 V	Н
$-0.2 \text{ V} < \text{V}_{\text{ID}} < 0.2 \text{ V}$	?
V <sub>ID</sub> ≤ -0.2 V	L
Open	Н

(1) H = High level, L = Low level, ? = Indeterminate

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#### 9 Application and Implementation

#### **NOTE**

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

#### 9.1 Application Information

Figure 7 shows a typical RS-422 application. One transmitter is able to broadcast to multiple receiving nodes connected together over a shared differential bus. Twisted-pair cabling with a controlled differential impedance is used, and a termination resistance is placed at the farthest receive end of the cable in order to match the transmission line impedance and minimize signal reflections.

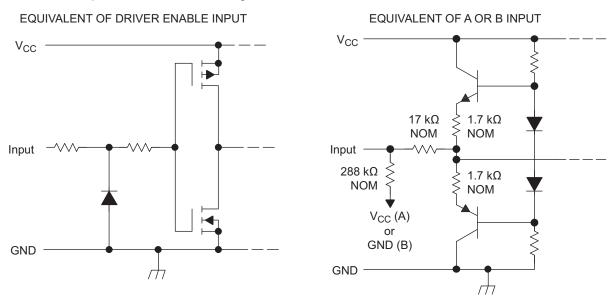


Figure 7. Schematic of Inputs



#### **Application Information (continued)**

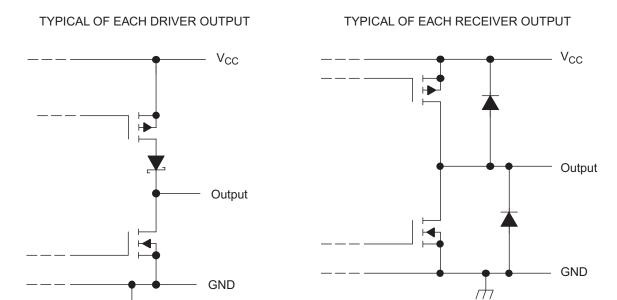


Figure 8. Schematic of Outputs

#### 9.2 Typical Application

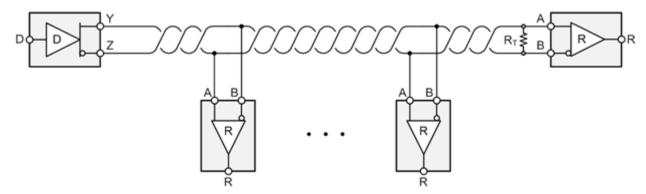


Figure 9. Typical RS-422 Application

#### 9.2.1 Design Requirements

A typical RS-422 implementation using SN65C116xE requires the following:

- 5-V power source.
- Connector that ensures the correct polarity for port pins.
- Cabling that supports the desired operating rate and transmission distance.

#### 9.2.2 Detailed Design Procedure

Place the device close to bus connector to keep traces (stub) short to prevent adding reflections to the bus line. If desired, add external fail-safe biasing to ensure ±200 mV on the A-B port when the driver circuit is disabled.

#### 10 Power Supply Recommendations

Use a 5-V power supply for  $V_{CC}$  place 0.1- $\mu$ F bypass capacitors close to the power supply pins to reduce errors coupling in from noisy or high impedance power supplies.

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## TEXAS INSTRUMENTS

#### 11 Device and Documentation Support

#### 11.1 Device Support

#### 11.1.1 Third-Party Products Disclaimer

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#### 11.3 Community Resources

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

TI E2E™ Online Community T's Engineer-to-Engineer (E2E) Community. Created to foster collaboration among engineers. At e2e.ti.com, you can ask questions, share knowledge, explore ideas and help solve problems with fellow engineers.

**Design Support** *TI's Design Support* Quickly find helpful E2E forums along with design support tools and contact information for technical support.

#### 11.4 Trademarks

E2E is a trademark of Texas Instruments.

All other trademarks are the property of their respective owners.

#### 11.5 Electrostatic Discharge Caution



These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

#### 11.6 Glossary

SLYZ022 — TI Glossary.

This glossary lists and explains terms, acronyms, and definitions.

#### 12 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

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#### PACKAGING INFORMATION

Orderable part number	Status	Material type	Package   Pins	Package qty   Carrier	RoHS	Lead finish/ MSL rating/ Ball material Peak reflow		Op temp (°C)	Part marking (6)
						(4)	(5)		
SN65C1168EMPWSEP	Active	Production	TSSOP (PW)   16	90   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-55 to 125	1168SEP
SN65C1168EMPWSEP.A	Active	Production	TSSOP (PW)   16	90   TUBE	Yes	NIPDAU	Level-3-260C-168 HR	-55 to 125	1168SEP
SN65C1168EMPWTSEP	Active	Production	TSSOP (PW)   16	250   SMALL T&R	Yes	NIPDAU	Level-3-260C-168 HR	-55 to 125	1168SEP
SN65C1168EMPWTSEP.A	Active	Production	TSSOP (PW)   16	250   SMALL T&R	Yes	NIPDAU	Level-3-260C-168 HR	-55 to 125	1168SEP
V62/19606-0XE	Active	Production	TSSOP (PW)   16	90   TUBE	-	NIPDAU	Level-3-260C-168 HR	-55 to 125	1168SEP
V62/19606-0XE-T	Active	Production	TSSOP (PW)   16	250   SMALL T&R	-	NIPDAU	Level-3-260C-168 HR	-55 to 125	1168SEP

<sup>(1)</sup> Status: For more details on status, see our product life cycle.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

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<sup>(2)</sup> Material type: When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

<sup>(3)</sup> RoHS values: Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

<sup>(4)</sup> Lead finish/Ball material: Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

<sup>(5)</sup> MSL rating/Peak reflow: The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

<sup>(6)</sup> Part marking: There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.



## **PACKAGE OPTION ADDENDUM**

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## **PACKAGE MATERIALS INFORMATION**

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#### TAPE AND REEL INFORMATION





	Dimension designed to accommodate the component width
В0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



#### \*All dimensions are nominal

Device	U	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
SN65C1168EMPWTSEP	TSSOP	PW	16	250	180.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

## **PACKAGE MATERIALS INFORMATION**

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#### \*All dimensions are nominal

	Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
Γ	SN65C1168EMPWTSEP	TSSOP	PW	16	250	213.0	191.0	35.0

## **PACKAGE MATERIALS INFORMATION**

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#### **TUBE**



#### \*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
SN65C1168EMPWSEP	PW	TSSOP	16	90	530	10.2	3600	3.5
SN65C1168EMPWSEP.A	PW	TSSOP	16	90	530	10.2	3600	3.5
V62/19606-0XE	PW	TSSOP	16	90	530	10.2	3600	3.5



SMALL OUTLINE PACKAGE



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

  2. This drawing is subject to change without notice.

  3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MO-153.



SMALL OUTLINE PACKAGE



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.



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